



STL40DN3LLH5

Dual N-channel 30 V, 0.016 Ω , 11 A
PowerFLAT™ (5x6) double island, STripFET™ V Power MOSFET

Preliminary data

Features

Type	V _{DSS}	R _{DS(on)}	I _D
STL40DN3LLH5	30 V	< 0.018 Ω	11 A ⁽¹⁾

1. The value is rated according R_{thj-pcb}

- R_{DS(on)} * Q_g industry benchmark
- Extremely low on-resistance R_{DS(on)}
- Very low switching gate charge
- High avalanche ruggedness
- Low gate drive power losses

Application

Switching applications

Description

This product utilizes the 5th generation of design rules of ST's proprietary STripFET™ technology. The lowest available R_{DS(on)} * Q_g, in this chip scale package, makes this device suitable for the most demanding DC-DC converter applications, where high power density is to be achieved.

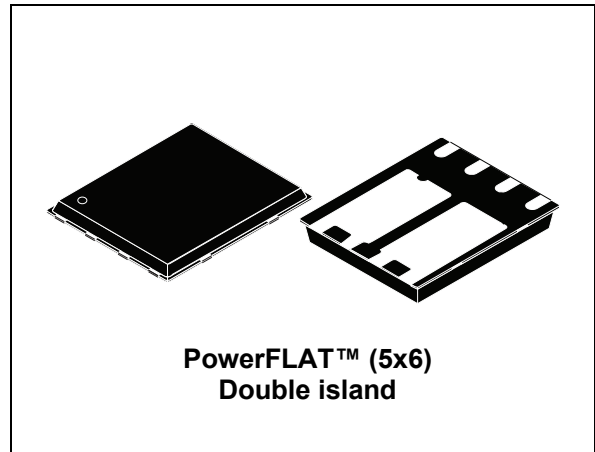


Figure 1. Internal schematic diagram

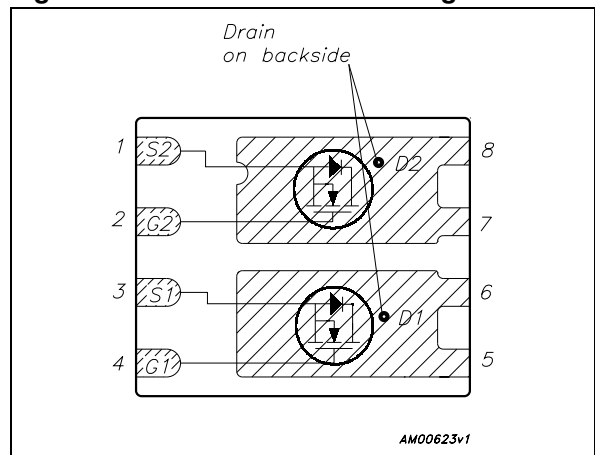


Table 1. Device summary

Order code	Marking	Package	Packaging
STL40DN3LLH5	40DN3LLH5	PowerFLAT™(5x6) Double island	Tape and reel

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	30	V
V_{GS}	Gate-source voltage	± 22	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	40	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	26	A
$I_D^{(2)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	11	A
$I_D^{(2)}$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	7	A
$I_{DM}^{(3)}$	Drain current (pulsed)	44	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25^\circ\text{C}$	60	W
$P_{TOT}^{(2)}$	Total dissipation at $T_C = 25^\circ\text{C}$	4	W
	Derating factor	0.03	W/ $^\circ\text{C}$
T_J	Operating junction temperature	-55 to 150	$^\circ\text{C}$
T_{stg}	Storage temperature		

1. The value is rated according R_{thj-c}
2. The value is rated according $R_{thj-pcb}$
3. Pulse width limited by safe operating area

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case (drain) (steady state)	2.08	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-ambient	32	$^\circ\text{C/W}$

1. When mounted on FR-4 board of 1inch², 2oz Cu, $t < 10$ sec

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0$	30			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$, $V_{DS} = \text{Max rating @ } 125^{\circ}\text{C}$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 22\ \text{V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	1	1.5		V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\ \text{V}$, $I_D = 5.5\ \text{A}$ $V_{GS} = 4.5\ \text{V}$, $I_D = 5.5\ \text{A}$		0.016 0.02	0.018 0.025	Ω Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\ \text{V}$, $f = 1\ \text{MHz}$, $V_{GS} = 0$	-	475	-	pF
C_{oss}	Output capacitance			97		pF
C_{rss}	Reverse transfer capacitance			19		pF
Q_g	Total gate charge	$V_{DD} = 15\ \text{V}$, $I_D = 11\ \text{A}$	-	4.5	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 4.5\ \text{V}$		1.7		nC
Q_{gd}	Gate-drain charge	(see Figure 3)		1.9		nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD}=15\text{ V}$, $I_D=11\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ (see Figure 2)	-	4	-	ns
t_r	Rise time			22		ns
$t_{d(off)}$	Turn-off delay time			13		ns
t_f	Fall time			2.8		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		11	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		44	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=11\text{ A}$, $V_{GS}=0$	-		1.1	V
t_{rr}	Reverse recovery time	$I_{SD}=11\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$, $V_{DD}=25\text{ V}$, $T_j=150\text{ }^\circ\text{C}$	-	16.2		ns
Q_{rr}	Reverse recovery charge			1		nC
I_{RRM}	Reverse recovery current			8.1		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

3 Test circuits

Figure 2. Switching times test circuit for resistive load

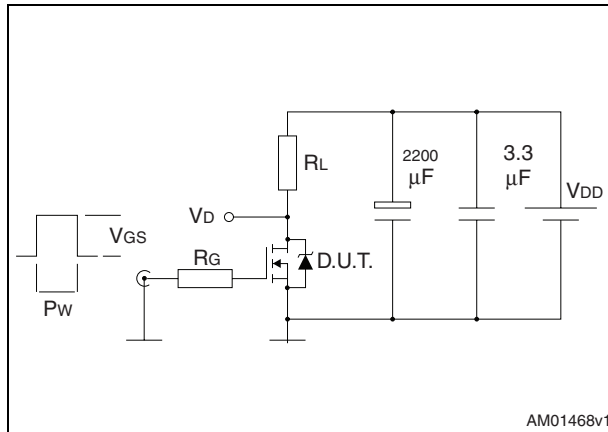


Figure 3. Gate charge test circuit

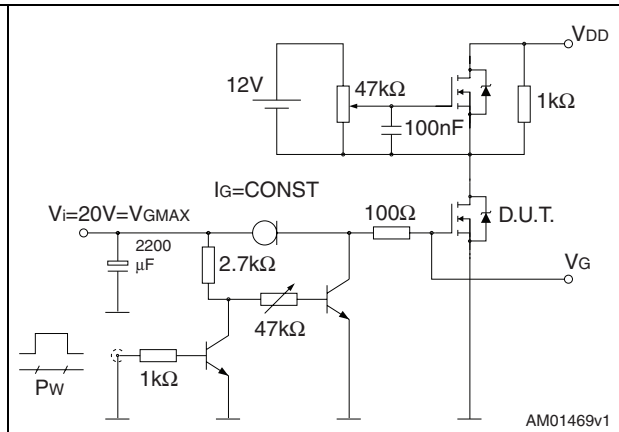


Figure 4. Test circuit for inductive load switching and diode recovery times

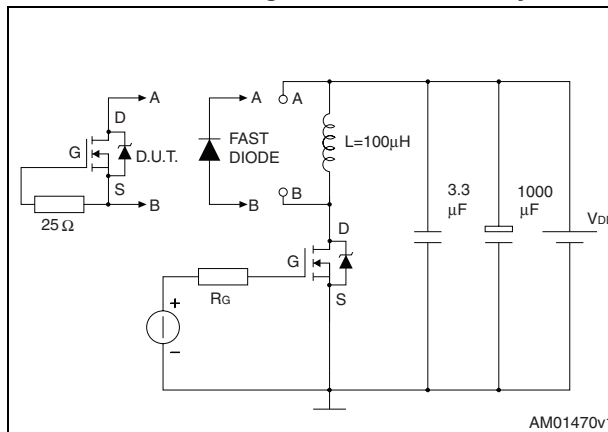


Figure 5. Unclamped inductive load test circuit

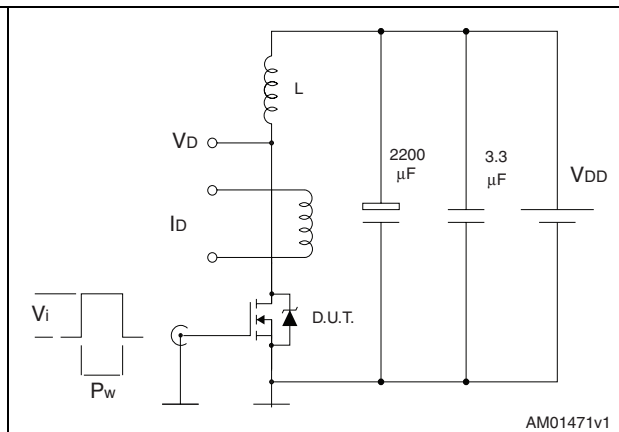


Figure 6. Unclamped inductive waveform

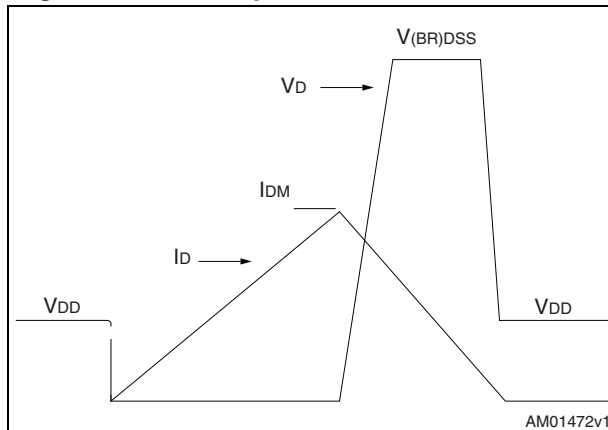
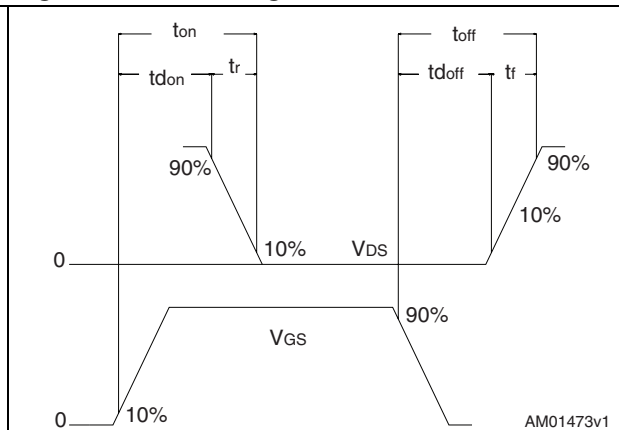


Figure 7. Switching time waveform



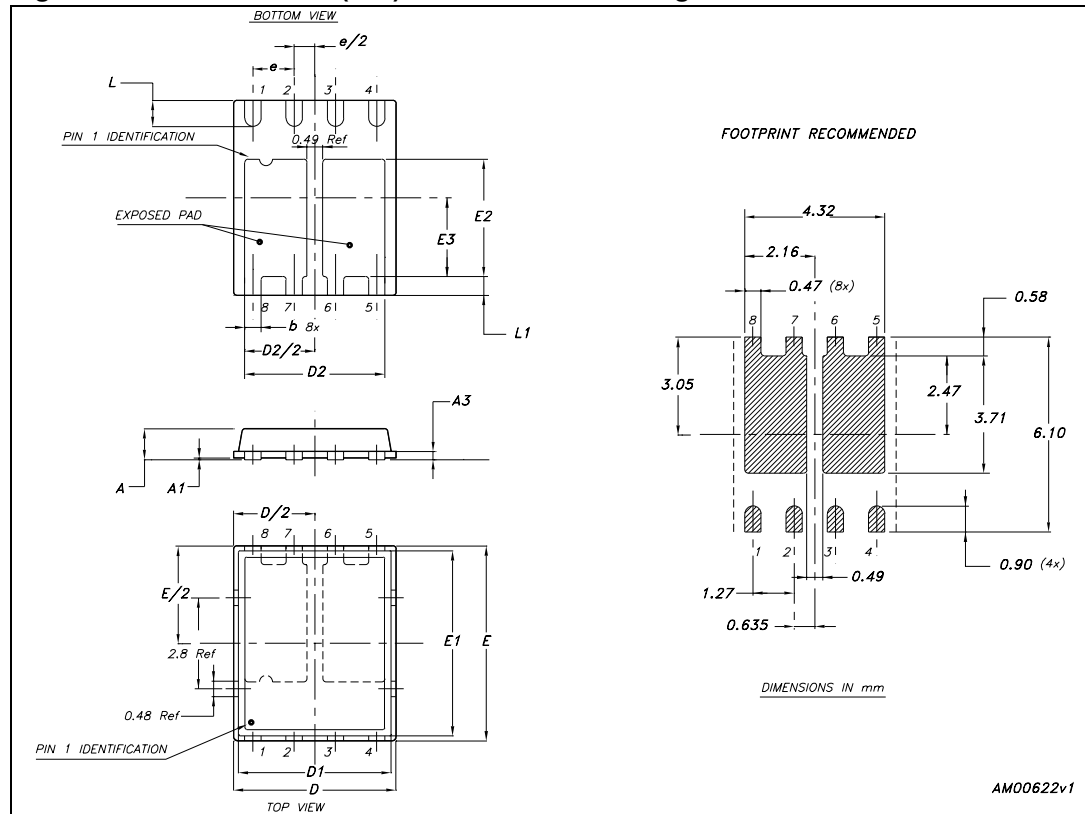
4 **Package mechanical data**

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 8. PowerFLAT™ (5x6) double island mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80	0.83	0.90
A1		0.02	0.05
A3		0.20	
b	0.35	0.40	0.47
D		5.00	
D1		4.75	
D2	4.11	4.21	4.31
E		6.00	
E1		5.75	
E2	3.51	3.61	3.71
E3	2.32	2.42	2.52
e		1.27	
L	0.70	0.80	0.90
L1	0.48	0.58	0.68

Figure 8. PowerFLAT™ (5x6) double island drawing



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
24-Jan-2011	1	First release

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